

Figure 3a depicts vertical measurement values of a wafer profile after etching with ethylene glycol/ HF 15% a spin etcher.

Figure 3b depicts horizontal measurement values of a wafer profile after etching with ethylene glycol/ HF 15% a spin etcher.

Figure 4a depicts vertical measurement values of a wafer profile after etching with ethylene glycol/glycerol/ HF 15% a spin etcher.

Figure 4b depicts horizontal measurement values of a wafer profile after etching with ethylene glycol/glycerol/ HF 15% a spin etcher.

IN THE CLAIMS

Please cancel claims 2, and 6:

Please amend claims 1, 3-5, and 7-8 as follows:

1. (Amended) An etching solution comprising 5- 20% by weight hydrofluoric acid, an organic solvent consisting essentially of, individually or as a mixture ethylene glycol, propylene glycol, ethanol, and glycerol, and 1-20 % by weight water for the production of integrated circuits.

3.(Amended) An etching solution according to claim 1, comprising only one an organic solvent selected from the group consisting of ethylene glycol, propylene glycol, ethanol, and glycerol.

4.(Amended) An Etching solution according to Claim 1, comprising, as organic solvent, ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.

5. (Amended) An Etching solution according to Claim 1, comprising, as organic solvent, ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.

7. (Amended) An Etching solution according to Claim 1, comprising a mixture of high-purity individual components.

B3
at 8. (Amended) A method for the selective etching of doped silicate layers comprising treating said doped silicate layers with an etching solution according to Claim 1.

Please add the following new Claims:

9. (New) A method according to claim 8, wherein said doped silicate is boron doped glass.

10. (New) A method according to claim 8, wherein said doped silicate is phosphorous doped glass.

B4 11. (New) A method according to claim 8, wherein said doped silicate is boron- phosphorous doped glass.

12. (New) A method according to claim 8, wherein said selective etching is carried out in a spin etcher.

13. (New) A method according to claim 8, wherein said selective etching is carried out in a drip etcher.